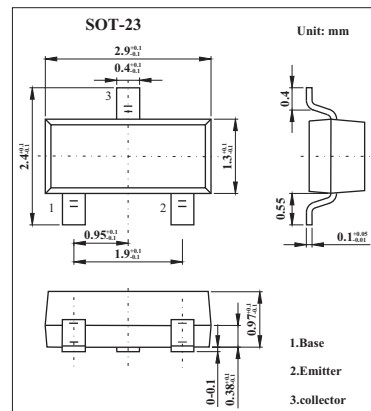


KC817-25

■ Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage
- Complementary types: KC807 (PNP)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	45	V
Emitter-base voltage	V _{EBO}	5	V
Collector current (DC)	I _c	500	mA
Peak collector current	I _{CM}	1	A
power dissipation	P _D	300	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _c = 10 μA, I _E = 0	50			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _c = 10 mA, I _B = 0	45			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _c = 0	5			V
Collector cutoff current	I _{CBO}	V _{CB} = 45 V, I _E = 0			100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = 5 V, I _c = 0			100	nA
DC current gain *	h _{FE}	V _{CE} = 1 V, I _c = 100 mA	160		400	
		V _{CE} = 1 V, I _c = 500 mA	40			
Collector saturation voltage *	V _{CE(sat)}	I _c = 500 mA, I _B = 50 mA			0.7	V
Base to emitter voltage *	V _{BE(sat)}	I _c = 500 mA, I _B = 50 mA			1.2	V
Collector-base capacitance	C _{ob}	V _{CB} = 10 V, f = 1 MHz		10		pF
Transition frequency	f _T	I _c = 10 mA, V _{CE} = 5 V, f = 100 MHz	100			MHz

* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ Marking

Marking	6BW
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